



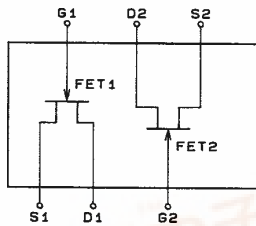
FC13

N-Channel Junction Silicon FET Low-Frequency General-Purpose Amp, Differential Amp, Analog Switch Applications

Features

- Composite type with 2 FETs contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC13 is formed with two chips, being equivalent to the 2SK303, placed in one package.
- Excellent in thermal equilibrium and pair capability and especially suited for differential amp.

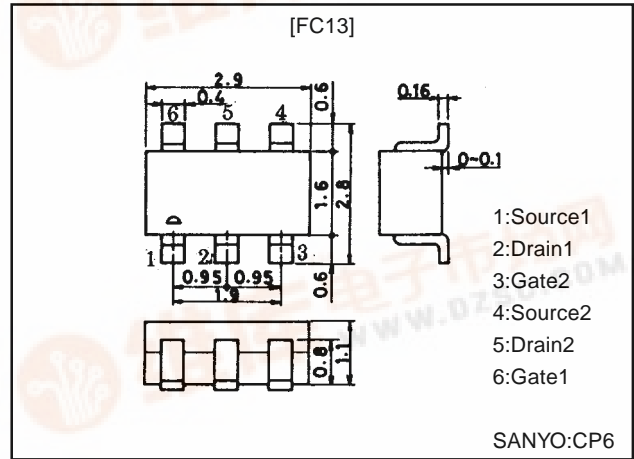
Electrical Connection



Package Dimensions

unit:mm

2095A



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSX}		30	V
Gate-to-Drain Voltage	V _{GDS}		-30	V
Gate Current	I _G		10	mA
Drain Current	I _D		10	mA
Allowable Power Dissipation	P _D	1unit	200	mW
Total Dissipation	P _T		300	mW
Junction Temperature	T _J		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
G-D Breakdown Voltage	V _{(BR)DGD}	I _G =-10μA, V _{DS} =0	-30			V
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =-20V, V _{DS} =0			-1.0	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1μA	-0.3	-0.9	-2.5	V
G-S Voltage Drop	ΔV _{GS}	V _{GS} (small/large), V _{DS} =10V, I _D =1mA			50	mV
Drain Current	I _{DSS}	V _{DS} =10V, V _{GS} =0	1.2*		6.0*	mA
Drain Current Ratio		V _{DS} =10V, I _{DSS} (small/large)	0.9			
Forward Transfer Admittance	Y _{fs}	V _{DS} =10V, V _{GS} =0, f=1kHz	3.0	5.0		mS
Forward Transfer Admittance Ratio		V _{DS} =10V, Y _{fs} (small/large)	0.9			
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0, f=1MHz		5.0		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =10V, V _{GS} =0, f=1MHz		0.9		pF
Static Drain-to-Source On-State Resistance	R _{DS(on)}	V _{DS} =10mV, V _{GS} =0		250		Ω

The specifications shown above are for each individual transistor.

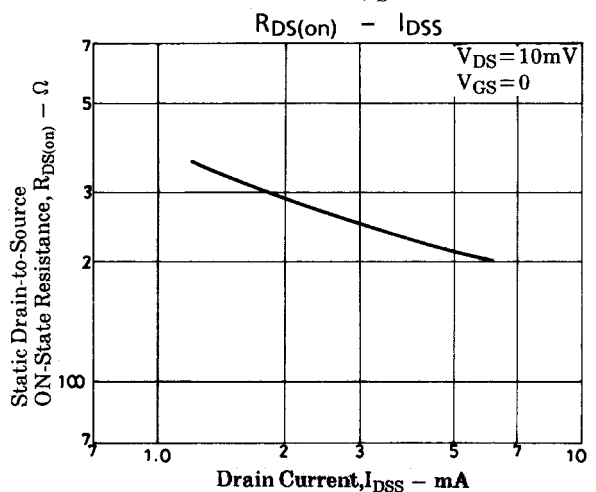
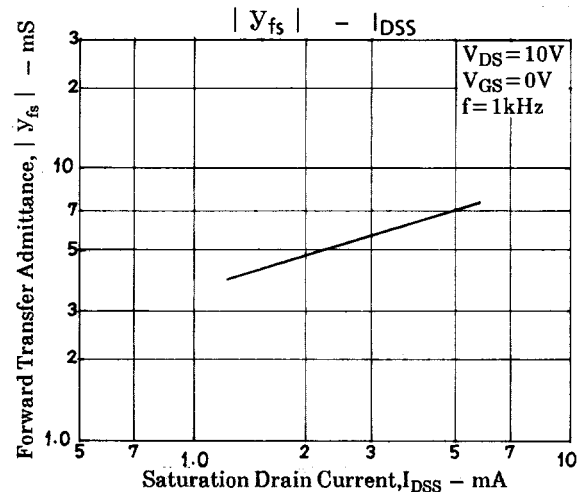
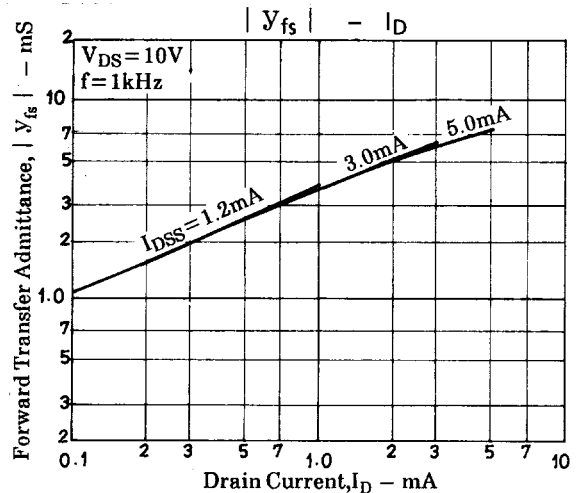
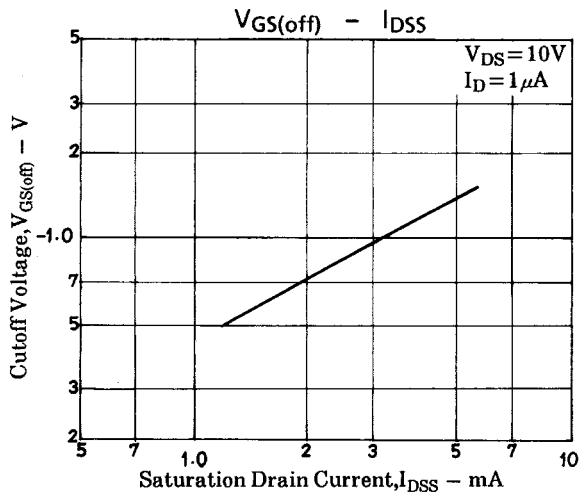
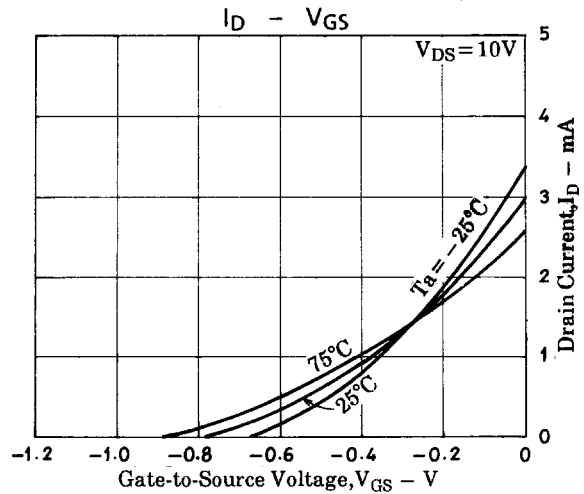
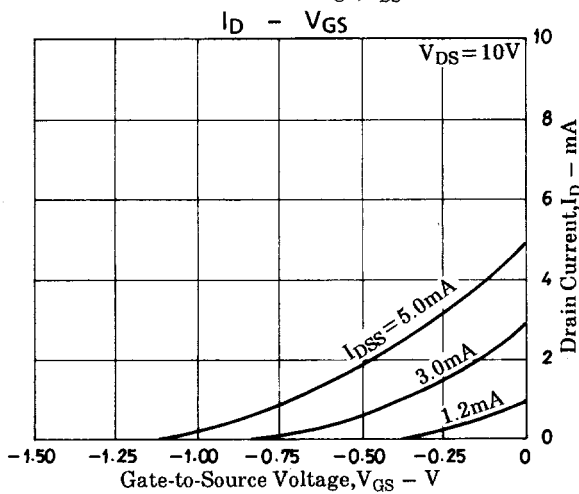
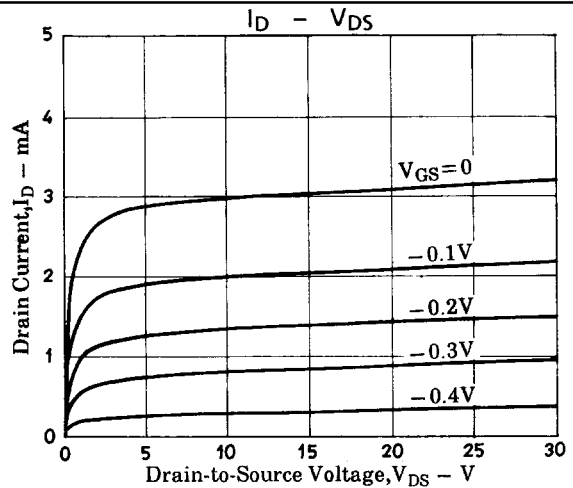
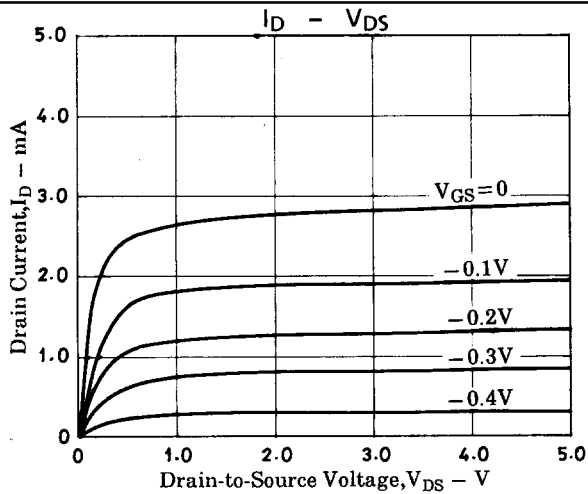
Marking:13

Note*:The FC13 is classified by FET1 I_{DSS} as follows :

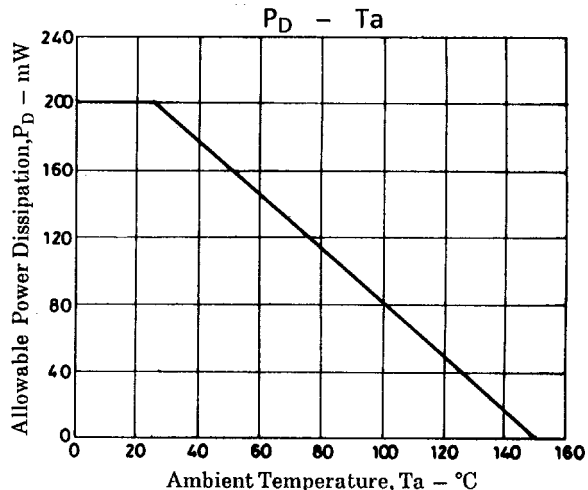
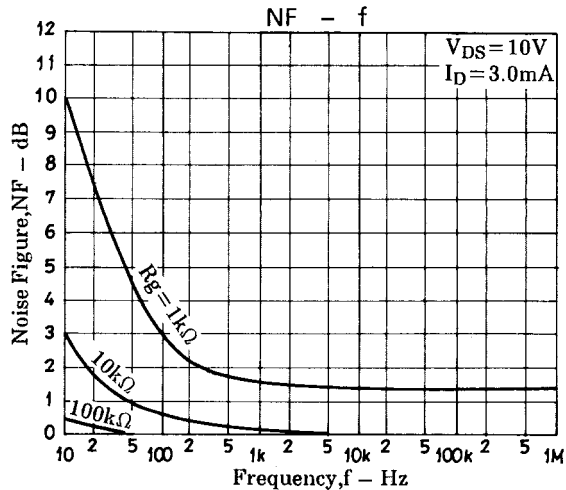
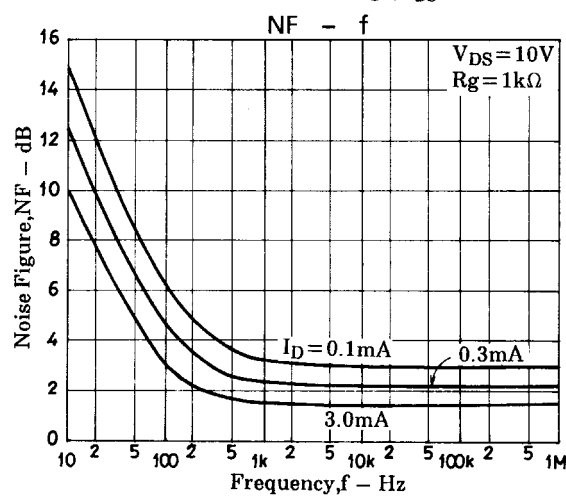
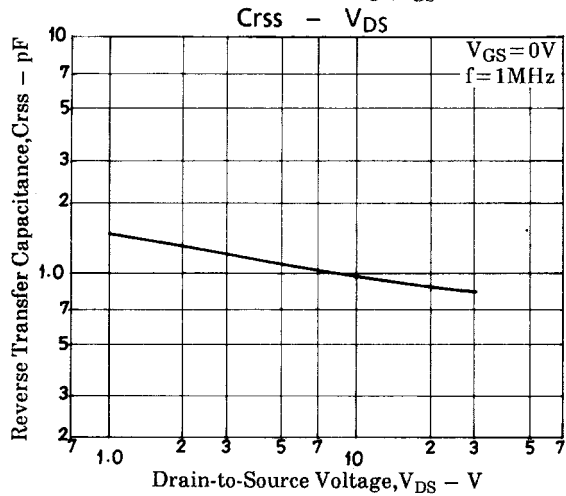
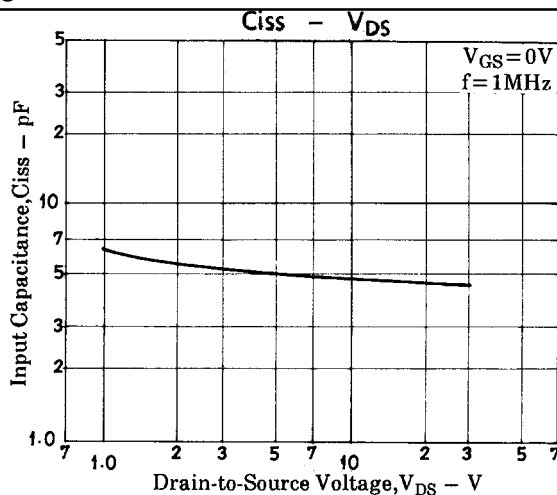
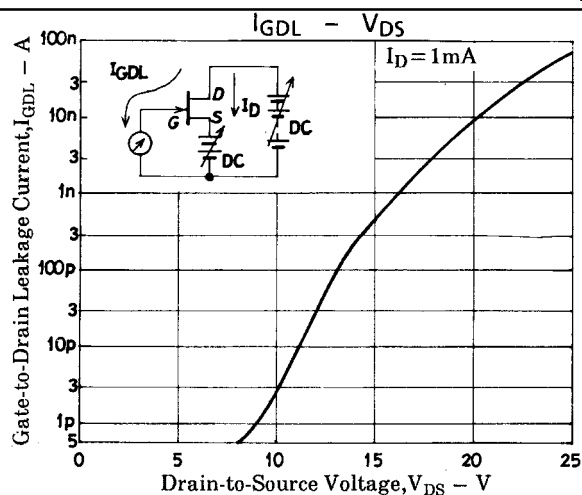
I_{DSS} rank:D,E

1.2	D	3.0	2.5	E	6.0
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FC13



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